Lawrence Berkeley National Laboratory

Recent Work

Title

A UNIVERSAL LAW FOR HIGH-TEMPERATURE DIFFUSION CONTROLLED TRANSIENT CREEP

Permalink

https://escholarship.org/uc/item/3kf9f0hg

Authors

Amin, Kamal E. Mukherjee, Amiya K. Dorn, John E.

Publication Date

1970

UCRL-19169 Preprint

*د،*2

RECEIVED
LAWRENCE
RADIATION LABORATORY

FEB 2 6 1970

LIBRARY AND CUMENTS SECTION

A UNIVERSAL LAW FOR HIGH-TEMPERATURE DIFFUSION CONTROLLED TRANSIENT CREEP

Kamal E. Amin, Amiya K. Mukherjee, and John E. Dorn
January 1970

AEC Contract No. W-7405-eng-48

TWO-WEEK LOAN COPY

This is a Library Circulating Copy which may be borrowed for two weeks. For a personal retention copy, call Tech. Info. Division, Ext. 5545

LAWRENCE RADIATION LABORATORY UNIVERSITY of CALIFORNIA BERKELEY

UCRL-19169

DISCLAIMER

This document was prepared as an account of work sponsored by the United States Government. While this document is believed to contain correct information, neither the United States Government nor any agency thereof, nor the Regents of the University of California, nor any of their employees, makes any warranty, express or implied, or assumes any legal responsibility for the accuracy, completeness, or usefulness of any information, apparatus, product, or process disclosed, or represents that its use would not infringe privately owned rights. Reference herein to any specific commercial product, process, or service by its trade name, trademark, manufacturer, or otherwise, does not necessarily constitute or imply its endorsement, recommendation, or favoring by the United States Government or any agency thereof, or the Regents of the University of California. The views and opinions of authors expressed herein do not necessarily state or reflect those of the United States Government or any agency thereof or the Regents of the University of California.

A UNIVERSAL LAW FOR HIGH-TEMPERATURE DIFFUSION CONTROLLED TRANSIENT CREEP

Kamal E. Amin, * Amiya K. Mukherjee, * and John E. Dorn *+

Inorganic Materials Research Division, Lawrence Radiation Laboratory, and Department of Materials Science and Engineering, College of Engineering, University of California, Berkeley, California

ABSTRACT

The transient creep at high temperatures is suggested to arise principally as a result of the dispersal of entanglements by the climb mechanism. The dispersal of the entanglements is assumed to follow a unimolecular reaction kinetics with a rate constant that depends on stress and temperature in the same way as does the secondary creep rate. The analysis shows that the strain ε , time t relation can be represented by:

$$\varepsilon = \varepsilon_0 + \dot{\varepsilon}_s t + \frac{\beta - 1}{K} \left[1 - e^{-K\dot{\varepsilon}_s t} \right]$$

where ϵ_0 is the instantaneous strain on loading; $\dot{\epsilon}_s$ the secondary creep rate, $K\dot{\epsilon}_s$ is the rate constant and β the ratio of initial to secondary creep rate. The experimental creep data on several body centered cubic

^{*} Research Assistant, IMRD of Lawrence Radiation Laboratory, University of California, Berkeley, California.

⁺ Associate Professor, Department of Mechanical Engineering, University of California, Davis, California.

⁺⁺ Professor of Materials Science, Department of Materials Science and Engineering and Senior Research Metallurgist, Inorganic Materials Research Division, Lawrence Radiation Laboratory, University of California, Berkeley, California.

and face centered cubic metals and alloys correlate quite well with the proposed mechanism. The constants β and K were found to be independent of temperature and stress. The proposed formulation becomes inapplicable for correlating creep data in polycrystals at low stresses because of the significant contribution of grain boundary sliding to the total creep at these stress levels.

I. INTRODUCTION

Most of the early investigations on high-temperature creep showed that

$$\varepsilon = \varepsilon \left\{ t \in \frac{-Q_c}{RT} \right\}$$
 for $\sigma = constant$ (1)

over both the transient and steady-state stages. Here ϵ is the total strain, which is the sum of the initial strain ϵ_0 upon stressing at t = 0 and the creep strain up to time t. The apparent activation energy, Q_c , for creep was shown to be insensitive to the stress, strain, grain size and temperature. The activation energy agreed very well with that for diffusion. The subsequent years produced extensive experimental evidence to confirm the validity of Eq. (1), but not much progress was achieved to further advance the understanding of the transient stage of creep. It is only over the last few years that several important observations have been made that have encouraged a more thorough analysis of transient creep.

For many materials the creep strain is found to follow Andrade's empirical equation, ² namely

$$\varepsilon - \varepsilon_0 = \dot{\varepsilon}_s t + B t^{1/3}$$
 (2)

where $\dot{\epsilon}_s$ is the steady-state creep rate and B is a constant. The formulation often appears to be in fair agreement with high temperature creep data. One objection to the universal application of Andrade's equation concerns its prediction of infinite initial creep rates. Although it is

admittedly difficult to measure the initial creep rates accurately, many carefully conducted experiments suggest that they are actually finite.

An alternative formulation that has been employed is:

$$\varepsilon - \varepsilon_0 = \varepsilon_s t + \varepsilon_T \left(1 - e^{-rt} \right) \tag{3}$$

where $\varepsilon_{\rm T}$ is the limiting transient strain and r is the ratio of the transient creep rate to the transient creep strain. Equation (3) was first suggested on a purely empirical basis by McVetty. The has been applied subsequently by Garafalo, Conway and Mulliken and by Evans and Wilshire.

It is the purpose of this report to provide a unified analysis for high-temperature creep that will incorporate the effect of both temperature and stress on the shape of transient creep curve. Section II of the report will summarize the pertinent substructural changes that accompany transient creep and will emphasize the role of dislocation climb in the dispersal of entanglements. Section III will be used to develop analytical theory for transient creep that is controlled by climb of dislocations based on unimolecular reaction-rate kinetics. The validity of the adoption of unimolecular rate kinetics will be justified in Section IV from correlation of experimental data.

II. SUBSTRUCTURAL CHANGES DURING TRANSIENT CREEP

A recent review of high-temperature creep reveals that only those metals and alloys that undergo initial straining upon stressing exhibit the usual normal transient stage of creep during which the creep rate progressively decreases to that for the steady-state. Those alloys which

do not undertake significant initial straining at t = 0 upon application of stress do not exhibit the usual normal transient stage. Instead, they display either a brief normal transient (BNT) or a brief inverted transient (BIT) or no transient behavior at all. Such BNT or BIT behavior, when present, usually does not extend beyond the first five or ten minutes of the test.

Therefore, normal transient creep rates appear to result from changes in the substructure from that which is produced immediately upon stressing to that which pertains to the steady state. The substructures which are formed upon initial straining at creep temperatures closely resemble those which are developed during strain hardening over stage III deformation at lower temperatures. Most of the dislocations are arranged in rough cellular patterns, the walls of which are composed of dislocation entanglements. Some cells contain a few randomly meandering dislocations in their interior.

Etch pitting studies ⁸,11 and electron microscopy ¹⁰⁻¹² have shown that dislocations rearrange themselves during the early part of transient creep as a result of the extra degree of freedom resulting from dislocation climb which becomes facile at high temperatures. Consequently, the entanglements disperse and adjacent cells coalesce so as to produce more sharply delineated subgrains which have a volume of about eight times that of the original cells. Over the secondary stage of creep an invariant substructure persists which depends only on the magnitude of the applied stress. It consists of subgrains separated from one another by low angle boundaries within which there exists a few isolated and randomly meandering dislocations.

The substructural changes that take place during normal transient creep are extremely complex. This is clearly revealed by the careful investigations of Clauer, Wilcox and Hirth. Changes in the different substructural details over the transient stage are obviously interrelated. The dispersal of entanglements, the build up of subboundaries, the changes in density of dislocations and the alterations in misorientations across subboundaries, etc., are not mutually independent. Among these various substructural details, only the changes in dislocation density have as yet been placed on a quantitative basis.

Changes in density of dislocations during transient creep have been studied by several investigators.^{8,11,13} It is difficult to accomplish this with satisfactory accuracy because of the major changes that take place in the geometrical distribution of dislocations. Also, it is not immediately obvious how the density of dislocations should be partitioned among those entangled in disappearing cell-walls, those joining the growing low-angle boundaries and those that are more or less randomly distributed. As the transient creep rate approaches that for the steady state, it is customary to count only those dislocations that are within the subgrains. But as shown by Clauer, Wilcox and Hirth, in moving tilt boundaries form a significant part of the substructure during transient creep of single crystals of Mo and consequently the dislocations in the subboundaries also deserve special attention. Although the state of knowledge concerning substructure is admittedly unsatisfactory, the available experimental data suggest that dislocation densities decrease only slightly during the dispersal of the entanglements in transient The decrease in creep rate during normal transient stage might

be assumed to indicate that strain hardening is taking place. Strain hardening, however, usually has the implication of increased density of dislocations. It therefore appears that the term recovery strengthening due to dispersal of entanglements by dislocation climb is preferable.

III. ANALYSIS

The substructural changes taking place during transient creep are so complex as to preclude any detailed mechanistic analysis of the process at this time. Although the dislocation density decreases over the transient stage of creep, it alone cannot account for the much greater percentage decrease in the creep rate. The major substructural change, as pointed out by Gupta and Strutt, centers about the dispersal of entanglements but the relationship between such dispersal and the transient creep rate is not yet understood. Undoubtedly all substructural changes during high-temperature transient creep are interrelated and dependent upon the dislocation climb mechanism. We therefore suggest that transient as well as steady-state creep is controlled by the rate of climb of dislocations. This is consistent with the validity of Eq. (1). Furthermore, we also assume that reactions taking place obey the laws of unimolecular kinetics. This assumption will be verified a posteriori.

Assuming that dislocation climb kinetics control transient creep the rate constant can be given in terms of the temperature and stress as $K\hat{\epsilon}_s$ where $\hat{\epsilon}_s$ is the steady-state creep rate as controlled by climb and K is a constant. As shown by Webster, Cox and Dorn the unimolecular can be formulated as:

$$\frac{d(\dot{\varepsilon} - \dot{\varepsilon}_{s})}{dt} = -K\dot{\varepsilon}_{s}(\dot{\varepsilon} - \dot{\varepsilon}_{s})$$
 (4)

Integrating Eq. (4) twice one obtains:

$$\varepsilon = \varepsilon_0 + \dot{\varepsilon}_s t + \frac{\dot{\varepsilon}_i - \dot{\varepsilon}_s}{K \dot{\varepsilon}_s} \quad \left(1 - e^{-K \dot{\varepsilon}_s t}\right)$$
 (5)

where $\dot{\epsilon}_i$ is the initial creep rate at t = 0, ϵ_0 is the initial strain upon stressing and

$$\frac{\dot{\varepsilon}_{i} - \dot{\varepsilon}_{s}}{K\dot{\varepsilon}_{s}} = \varepsilon_{T} \tag{6}$$

where $\epsilon_{\rm T}$ is the transient strain. Since the transient and steady-state stages have the same energy of activation and also the same kinetics of reaction as implied by Eq. (1) it follows necessarily that $\dot{\epsilon}_{\rm i}$ = β $\dot{\epsilon}_{\rm s}$ where β is a constant greater than unity. Therefore the total transient strain

$$\varepsilon_{\mathrm{T}} = \frac{\dot{\varepsilon}_{\mathrm{i}} - \dot{\varepsilon}_{\mathrm{s}}}{K\dot{\varepsilon}_{\mathrm{s}}} = \frac{\beta - 1}{K} \tag{7}$$

where β , K are constants independent of stress and temperature. A significant implication of Eq. (7) is that although $\dot{\epsilon}_i$ and $\dot{\epsilon}_s$ are both functions of stress, ϵ_{τ} is a constant and like β and K is independent

of stress and temperature.

According to the above analysis, the following must apply:

- l. The initial strain upon stressing, ϵ_0 is athermal and depends on the original state of the metal or alloy and the value of σ/G where σ is the stress and G is the shear modulus.
- 2. The ratio of the initial to secondary creep rates β , is a constant independent of stress, temperature and initial strain.
- 3. The rate of dispersal of the entanglements depends on the same function of stress and temperature as does the secondary creep rate.
- 4. For a given metal or alloy the transient strain ε_T is constant independent of stress or temperature.
- 5. For a given metal or alloy there exists a universal high temperature transient and steady-state creep curve of the form

$$\varepsilon - \varepsilon_0 = f(\dot{\varepsilon}_s t) = \phi \left[(\sigma/G)^n \frac{DGb}{kT} t \right]$$
 (8)

where the function f is derived from the general equation

$$\frac{\dot{\varepsilon}_{S} kT}{DGb} = Constant \left(\sigma/G\right)^{n}$$

as shown to be valid by a general survey 15 on secondary creep. Here D is the diffusivity, b is the Burgers vector, n is the stress dependence of secondary creep rate and kT has the usual meaning of Boltzmann constant times absolute temperature. The relationship depicted in Eq. (8)

is an extension of Eq. (1), which now incorporates the effects of stress as well as temperature on the shape of transient creep curve.

IV. CORRELATION WITH EXPERIMENTAL DATA

A careful survey and reanalysis was made of all the experimental results on high-temperature transient creep where the pertinent data on diffusivity and shear modulus were also available. A summary of all the examples that have been analyzed is given in Table I.

The validity of Eq. (5) is shown by the creep curves depicted in Fig. 1 (a) through (f) for experimental data on Al, 16 Ag, 17 purified Fe, ¹⁸ Fe containing carbon, ¹⁹ Cu, ²⁰ plain carbon steel, ²¹ Mo single crystals, 22 low carbon Ni, 24 Pt 26 and stainless steel. 12 In general, the data spanned a range of stress levels and in the case of data on Pt, low carbon Ni, Al, Ag, and Fe containing carbon, a range of temperatures as well. The creep curves clearly reveal that regardless of temperature and stress, the data for each material falls well on a single curve which agrees well with the solid theoretical curve of Eq. (5). Figure 2 shows the initial strain, ε_0 , as a function of (σ/G) for the cases that were analyzed. These data refer to the modulusadjusted athermal stress-strain curves at high temperatures. These data show considerable scatter, primarily because of difficulties in determining the initial strains immediately following stressing. The secondary creep rates $\dot{\epsilon}_{\rm s}$, for the metals and alloys in question are shown in Fig. 3, where log $\hat{\epsilon}_s kT/DGb$ is plotted as a function of log σ/G . The curves agree fairly well with similar curves that were presented in a recent review. There is some scatter in the data, particularly that for Pt and to a lesser extent in Al, both of which showed somewhat

higher stress dependence of the secondary creep rates than were reported earlier. The plot for Ag on the other hand revealed a lesser stress dependence of $\dot{\epsilon}_s$. In general, however, the plots clearly fall into the category of creep as controlled by the dislocation-climb mechanism.

A typical example of the universal creep curve for the case of polycrystalline Ni is shown by the datum points of Fig. 4(a). Regardless of stress and temperature all data fall well on a single curve. The solid line refers to the theoretical expression given by Eq. (8). An even more convincing proof of the validity of the universal creep curve is shown in Fig. 4(b) for Nb, where the experimental data cover ranges of temperature as well as stress and the secondary creep rates vary by two orders of magnitude. The remaining cases that were examined were about equally consistent and illustrated the good agreement of the theory with the experimental results.

The stress dependence of $\dot{\epsilon}_i$ and $\dot{\epsilon}_s$ is shown in Fig. 5 where $\dot{\epsilon}$ kT/DGb is plotted against σ /G in dimensionless units. The datum points refer to creep of Ni ²³ at one temperature and five stress levels and to creep of Nb²⁵ for a series of temperature or stress levels. The figure illustrates that the initial creep rates, $\dot{\epsilon}_i$, for a series of stresses and temperatures are greater than the secondary creep rates, $\dot{\epsilon}_s$, by a constant factor β . Both $\dot{\epsilon}_i$ and $\dot{\epsilon}_s$ are dependent on the substructural details that develop and hence are functions of stress. As shown in Fig. 5, their difference is a constant regardless of stress and temperature and is not a function of state.

Values for the transient strain ϵ_T were deducted from curves in Figs. l(a-f) and Fig. 4(a-b). The rate constant K for different cases was determined at one half of the transient strain ϵ_T where Eq. (5) becomes K = ln 2/ ϵ_S t. The calculated values for the constants K, β and ϵ_T are shown in Table I. Whereas the transient strain ϵ_T exhibits rather pronounced variations from case to case, the rate constant K seems to be somewhat less variable. Undoubtedly both depend on significant substructural details . Up to the present, however, no consistent trends in variations of K or β have been uncovered relative to effect of grain size, stacking-fault energies, or any other pertinent structural details.

Evans and Wilshire onted that Eq. (5) becomes inaccurate for creep of polycrystalline iron at low stresses. Similar discrepancies, which are observed in the creep of austenitic stainless steel, have been shown by Webster, Cox and Dorn lh to arise from the increased contribution of grain boundary sliding to the total creep rate at the low applied stresses. (The data for stainless steel by Garofalo were analyzed here only at higher stress levels where the contribution of grain boundary sliding is less than 0.04 of the total creep strain.) When grain boundary sliding prevails, Ke_s is no longer the pertinent rate constant since it refers to a creep mechanism resulting from climb alone. Once grain boundary sliding is better understood quantitatively, this factor might also be taken into consideration so as to completely account for high temperature transient creep at low stresses in polycrystals as well.

V. CONCLUSIONS

1. It has been shown that the creep equation

$$\varepsilon = \varepsilon_0 + \dot{\varepsilon}_s t + \varepsilon_T \left[1 - e^{-K\dot{\varepsilon}_s t} \right]$$

can be derived from the assumption that transient creep follows a first order kinetic reaction rate theory, with a rate constant that depends on stress and temperature in the same way as does the secondary creep rate.

- 2. High-temperature transient creep is suggested to result from substructural modifications due to stress and diffusion controlled climb of dislocations.
- 3. For a given metal or allow there exists a universal high temperature transient and steady-state creep curve that incorporates the effect of temperature as well as stress in the general form of

$$\varepsilon = \varepsilon_0 + f(\dot{\varepsilon}_s t) = \phi \left[(\sigma/G)^n \cdot \frac{DGb}{kT} t \right] + \varepsilon_0$$

- 4. For any given metal or alloy the transient strain ϵ_T is constant independent of stress or temperature.
- 5. The initial creep rate $\dot{\epsilon}_i$ for a given metal or alloy is a constant multiple, β , of the steady-state creep rate $\dot{\epsilon}_s$, regardless of stress and temperature.
- 6. The initial strain ϵ_0 depends on the original state of the metal or alloy and the value of (σ/G) .

7. In polycrystals at low stress levels, $K\dot{\epsilon}_S$ is no longer the pertinent rate constant and the effect of grain boundary sliding need yet be taken into consideration.

REFERENCES

- 1. J. E. Dorn, J. Mech. Phy. Solids, 3, 85 (1954).
- 2. E. N. da C Andrade: Proc. Roy. Soc. (London), Ser. A, 84, 1-12, (1910).
- 3. P. G. McVetty, Mech. Eng., <u>56</u>, 149, (1934).
- 4. F. Garofalo, <u>Fundamentals of Creep and Creep-Rupture in Metals</u>,
 MacMillan, New York (1965).
- 5. J. B. Conway and M. J. Mulliken, Trans. AIME, 236, 1496 (1966).
- 6. W. T. Evans and B. Wilshire, Trans. AIME, <u>242</u>, 1303 (1968).
- 7. James E. Bird, Amiya K. Mukherjee and John E. Dorn, "Correlations Between High-Temperature Creep Behavior and Substructure," presented at the International Conference on "Quantitative Relation Between Properties and Microstructure," Haifa, Israel, July 27-August 1, 1969.
- 8. V. P. Gupta and P. R. Strutt, Canad. J. Phys., 45, 1213 (1967).
- 9. J. D. Livington, Acta Met., <u>10</u>, 229 (1962).
- 10. F. H. Hammad and W. D. Nix, Trans. ASM, <u>59</u>, 94 (1966).
- 11. A. H. Clauer, B. A. Wilcox and J. P. Hirth, "Dislocation Substructure Induced by Creep in Molybdenum Single Crystals," to be published in Acta Met.
- 12. F. Garfalo, C. Richmond, W. F. Domis and V. Gemingen, "Joint International Conference on Creep," p. 1-31, J. Mech. Eng., (London), (1963).
- 13. C. R. Barrett, W. D. Nix and O. D. Sherby, Trans. ASM, <u>59</u>, 3 (1966).

- 14. G. A. Webster, A. P. D. Cox and J. E. Dorn, "Relationship Between Transient and Steady-State Creep at Elevated Temperatures," to be published.
- 15. A. K. Mukherjee, J. E. Bird and J. E. Dorn, Trans. AIME, <u>62</u>, 155, (1969).
- 16. O. D. Sherby, T. A. Trozera and J. E. Dorn, Proc. ASTM, <u>56</u>, 789 (1956).
- 17. R. P. Carreker and R. W. Guard, "Creep of Silver Wire," General Electric Co. Report No. 55-RL-1414 (Nov. 1955).
- 18. F. Garofalo, L. Zwell, A. S. Keh and S. Weissmann, Acta Met., 9, 721 (1961).
- 19. D. McLean and K. F. Hale, "Structural Processes in Creep," The Iron and Steel Institute, p. 19, 1961.
- 20. P. Feltham and J. D. Meakin, Acta Met., 7, 614 (1959).
- 21. P. Feltham, in Proc. 2nd International Conference on Rheology, Oxford, July 1953, p. 266. Butterworth, London (1954).
- 22. Unpublished data of reference 15.
- 23. E. R. Parker, Trans. ASM, 50, 85 (1958).
- 24. Phillip Coldren and James W. Freeman, "A Study of Substructure and Creep Resistance Using Ni, with Preliminary Data for Nb," ASD

 Technical Report 61-440, November 1961, The University of Michigan.
- 25. G. Brinson and B. Argent, J. Inst. Metals, <u>91</u>, 293 (1962-63).
- 26. R. P. Carreker, Jr., J. Appl. Phys., 21, 1289 (1950).

FIGURE CAPTIONS

- Fig. 1. Experimental data for Eq. (5) as ϵ ϵ_0 versus $\dot{\epsilon}_s t$.
- Fig. 2. Initial strain ϵ_0 , versus (σ/G).
- Fig. 3. The stress dependence of the secondary creep rate $\dot{\epsilon}_{_{\rm S}}$ plotted as

 $\frac{\epsilon_{s}kT}{DGb} \quad \text{versus Log (o/G).}$

- Fig. 4. The Universal Creep Curve.
- Fig. 5. The stress dependence of $\dot{\epsilon}_i$ and $\dot{\epsilon}_s$ for Nb and Ni plotted in dimensionless units.

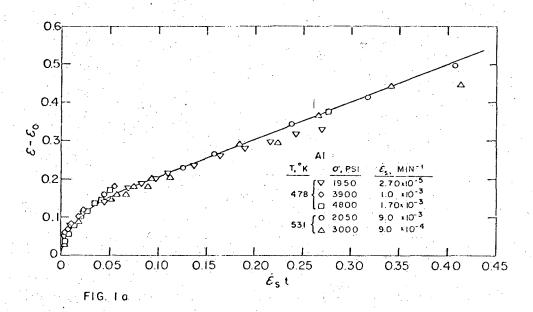
ACKNOWLEDGMENT

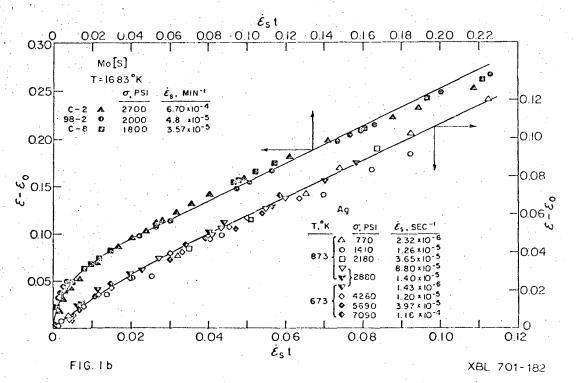
The authors express their appreciation to the United States

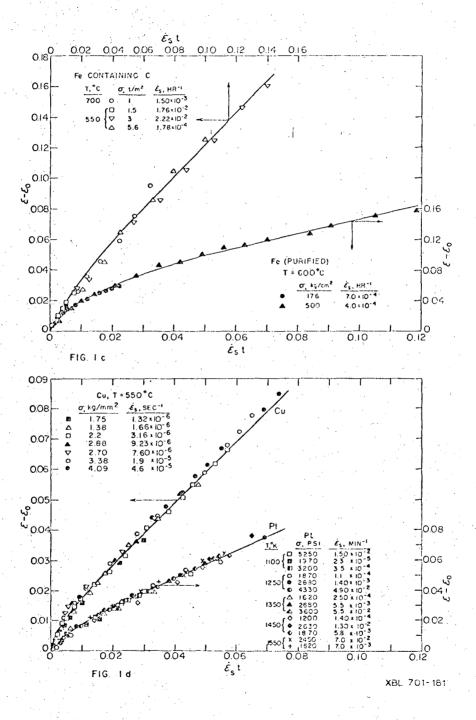
Atomic Energy Commission for their support of this research effort
through the Inorganic Materials Research Division of the Lawrence
Radiation Laboratory of the University of California, Berkeley,
California.

Table I. Summary of Analyzed Transient Creep Data

Metal (Polycrystalline)	Crystal Structure	Grain Size (mm)	$\epsilon_{ m T}$	K	β	Chemical Composition	- Ref	
Al	F.c.c.	0.21	0.105	82	9.56		16	
Ag	F.c.c.	0.017	0.013	99	2,28		17	
Alpha-Fe	B.c.c.		0:053	92.5	5.9	C, N <50 p.p.m., total impurity <100 p.p.m.	18	·
α - Fe	B.c.c.	0.025	0.017	82.5	2.4	C: 0.054, N: 0.0005, O: 0.0005, Si: 0.013, S: 0.0026, P: 0.001, Mn: 0.001, Al: 0.006	19	
Cu	F.c.c.	0.03	0.0085	277	3.35	Fe: 40 p.p.m, S: 8, Ag: 6, Ni: 5, Pb: 4	20	-17-
Plain C - Steel	B.c.c.	austenitic grain size 0.21-0.104	0.024	116	3.77	C: 0.23, Si: 0.13, Mn: 0.60, S: 0.036, P: 0.036, cr: 0.092 Ni: 0.17 and Cu: 0.125%	21	
Mo,[S] Single crystal	B.c.c.		0.052	173	10.00		22	-
Ni low c - Ni	F.c.c. F.c.c.		0.042	346 330	12.9 12.88	C: 0.01, Mn: 0.03, Si: 0.1	23 24	U.
Nb Nb	B.c.c.	0.17 - 0.36	0.032	173.2	10.2	C: <0.015, 0: 0.076, Ta: <0.25	25	UCRL-19169
Pt	F.c.c.		0.01	138.6	2.39	Traces of Fc, Pd <0.01 wt %	26	169
Stainless Steel	F.c.c.	0.09	0.065	34.60	3.26		12	







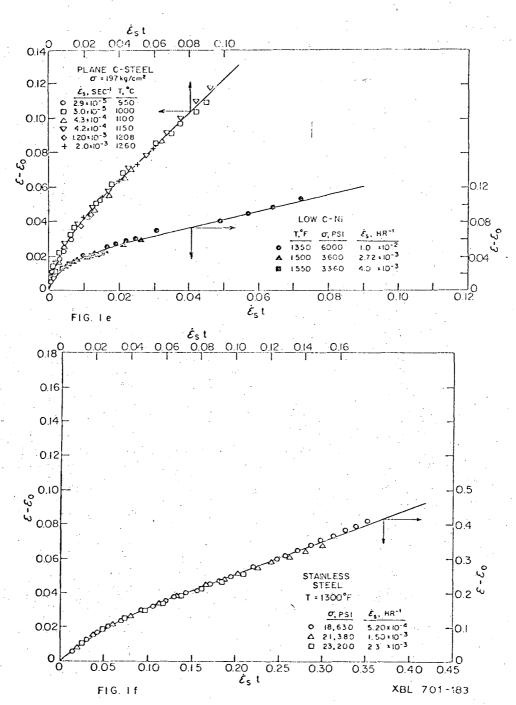


FIG. 1 EXPERIMENTAL DATA FOR EQUATION (5) AS $\dot{\epsilon}$ - $\dot{\epsilon}_{\rm o}$ vs. $\dot{\dot{\epsilon}}_{\rm s}$ t

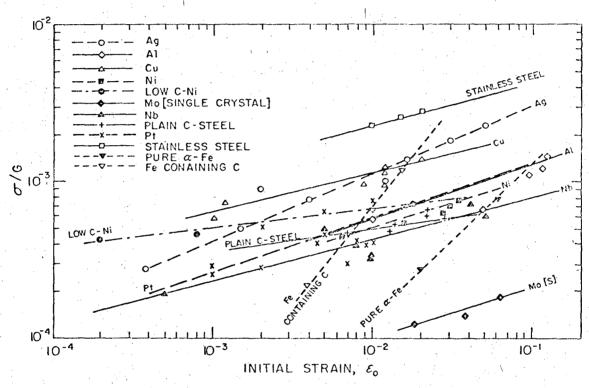


FIG 2 INITIAL STRAIN, ε , vs. σ/G .

XBL 701-178

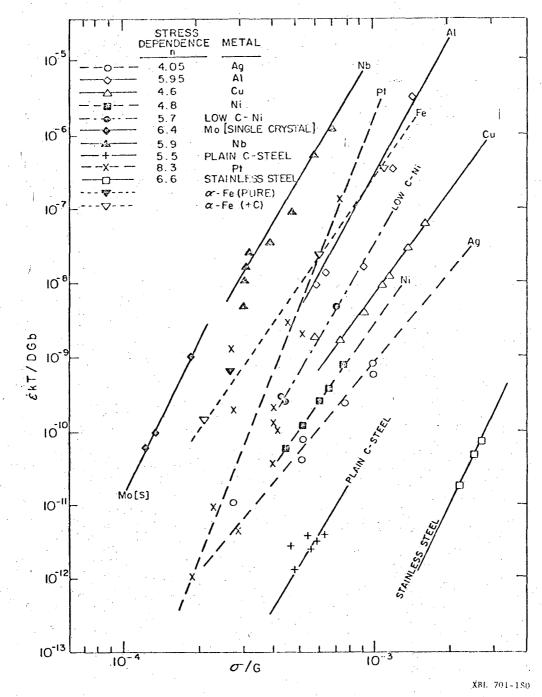


FIG. 3 STRESS DEPENDENCE OF SECONDARY CREEP RATE.

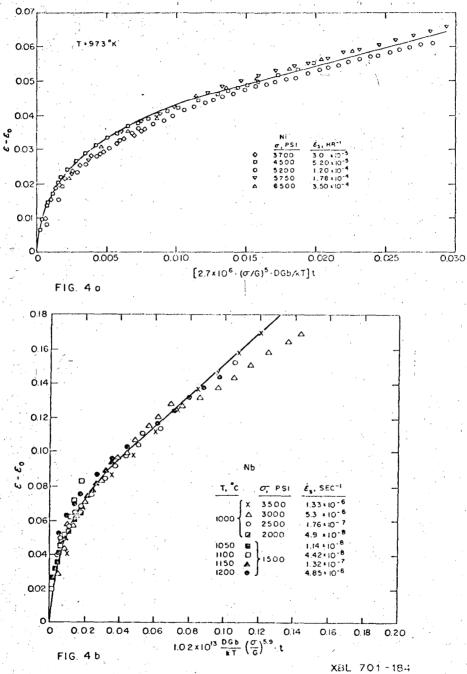


FIG. 4 THE UNIVERSAL CREEP CURVE.

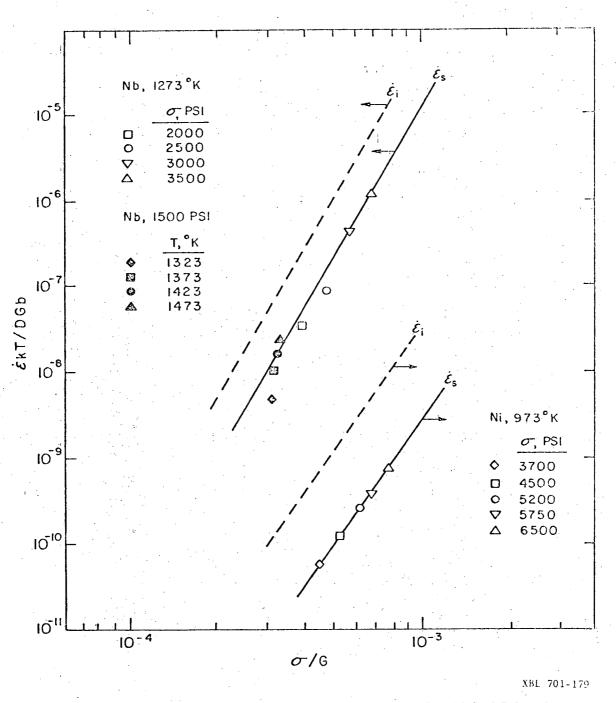


FIG. 5 THE STRESS DEPENDENCE OF INITIAL AND SECONDARY CREEP RATE FOR Nb AND Ni.

LEGAL NOTICE

This report was prepared as an account of Government sponsored work. Neither the United States, nor the Commission, nor any person acting on behalf of the Commission:

- A. Makes any warranty or representation, expressed or implied, with respect to the accuracy, completeness, or usefulness of the information contained in this report, or that the use of any information, apparatus, method, or process disclosed in this report may not infringe privately owned rights; or
- B. Assumes any liabilities with respect to the use of, or for damages resulting from the use of any information, apparatus, method, or process disclosed in this report.

As used in the above, "person acting on behalf of the Commission" includes any employee or contractor of the Commission, or employee of such contractor, to the extent that such employee or contractor of the Commission, or employee of such contractor prepares, disseminates, or provides access to, any information pursuant to his employment or contract with the Commission, or his employment with such contractor.

TECHNICAL INFORMATION DIVISION LAWRENCE RADIATION LABORATORY UNIVERSITY OF CALIFORNIA BERKELEY, CALIFORNIA 94720